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(71) Applicant: **SILTRONIC AG** [DE/DE]; Einsteinstr. 172
Tower B / Blue Tower, 81677 München (DE).

(72) Inventors: **KÖSTER, Ludwig**; Bachstr. 4, 84489
Burghausen (DE). **VOLLKOPF, Alexander**; Marktler
Str. 74, 84489 Burghausen (DE). **KOMODA, Mitsunori**;
Robert-Koch-Str. 75, 84489 Burghausen (DE).

(74) Agent: **STAUDACHER, Wolfgang**; Johannes-Hess-Str.
24, 84489 Burghausen (DE).

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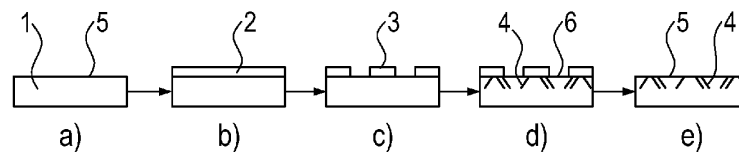
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(54) Title: METHOD FOR TESTING THE STRESS ROBUSTNESS OF A SEMICONDUCTOR SUBSTRATE

Fig. 1



(57) Abstract: Method for testing the stress robustness of a semiconductor substrate, comprising forming a nitride layer on a surface of the semiconductor substrate; patterning the nitride layer into a patterned nitride by photolithography including a step of reactive ion etching with ions produced from a gas which comprises hydrogen or a hydrogen compound or both; processing the patterned nitride and the semiconductor substrate at a temperature of not less than 800 °C and not more than 1300 °C to induce the formation of dislocations at an interface between the patterned nitride and the semiconductor substrate; and evaluating at least one property that is related to the formed dislocations.

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